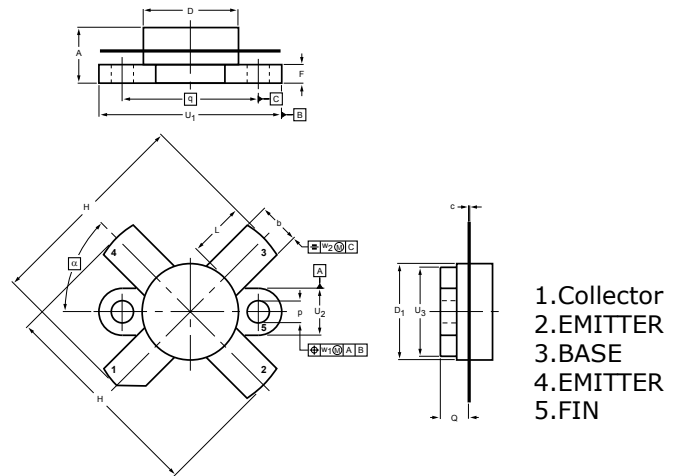


DESCRIPTION

Designed For HF Band SSB LINEAR
POWER AMPLIFIER APPLICATIONS

FEATURES

- Specified 12.5V, 28MHz Characteristics
- $P_o = 60W$ PEP(Min.)
- $G_p = 13.8$ dB (Typ) @28M
- Omnigold™ Metalization System



DIMENSIONS

NOTE: ALL ELECTRODES ARE ISOLATED FROM FLANGE.

UNIT	A	b	c	D	D ₁	F	H	L	p	Q	q	U ₁	U ₂	U ₃	w ₁	w ₂	α
mm	7.27	5.82	0.16	12.86	12.83	2.67	28.45	7.93	3.30	4.45	18.42	24.90	6.48	12.32	0.51	1.02	45°
	6.17	5.56	0.10	12.59	12.57	2.41	25.52	6.32	3.05	3.91		24.63	6.22	12.06			
inches	0.286	0.229	0.006	0.506	0.505	0.105	1.120	0.312	0.130	0.175	0.725	0.98	0.255	0.485	0.02	0.04	
	0.243	0.219	0.004	0.496	0.495	0.095	1.005	0.249	0.120	0.154		0.97	0.245	0.475			

MAXIMUM RATINGS

CHARACTERISTICS	SYMBOL	RATINGS	UNITS
Collector-Base Voltage	V_{CB0}	55	V
Collector-Emitter Voltage	V_{CES}	45	V
Collector-Emitter Voltage	V_{CEO}	18	V
Collector Current	I_C	20	A
Emitter-Base Voltage	V_{EBO}	4.5	V
Collector Power Dissipation	P_{DISS}	175	W
Junction Temperature	T_J	-65 to 175	°C
Storage Temperature Range	T_{STG}	-65 to 175	°C

ELECTRICAL CHARACTERISTICS

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Collector-Emitter Breakdown Voltage	$eV_{(BR)CEO}$	$I_C=100mA, I_B=0$	18	-	-	V
Collector-Emitter Breakdown Voltage	$eV_{(BR)CES}$	$I_C=100mA, V_{EB}=0$	45	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=1mA, I_C=0$	4.5	-	-	V
Collector Cutoff Current	I_{CBO}	$V_{CB} = 30V, I_E = 0$	-	-	500	uA
DC Current Gain	h_{FE}	$V_{CE}=5V, I_C=10A$	10	-	-	
Power Gain	G_p	$V_{CC}=12.5V, P_{OUT}=60W, f=28MHz, P_{IN}=2.5W$	11.8	13.8	-	dB
Collector Efficiency	η_C		35	-	-	%
Intermodulation Distortion	IMD		-	-	-30	dB
Collector Output Capacitance	C_{ob}	$V_{CB}=12.5V, I_E=0, f=1MHz$	-	-	500	pF

Note : Above parameters , ratings , limits and conditions are subject to change.